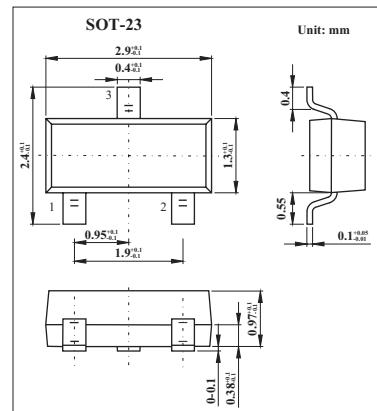


High Conductance Ultra Fast Diode

**MMBD1201; MMBD1203
MMBD1204; MMBD1205**

■ Features



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W _{IV}	50	V
Average Rectified Current	I _o	200	mA
DC Forward Current	I _F	600	mA
Recurrent Peak Forward Current	i _f	700	mA
Peak Forward Surge Current			
Pulse width = 1.0 second	i _{f(surge)}	1.0	A
Pulse width = 1.0 microsecond		2.0	A
Storage Temperature Range	T _{stg}	-55 to + 150	°C
Operating Junction Temperature	T _J	150	°C
Total Device Dissipation	P _D	350	mW
Derate above 25 °C		2.8	mW / °C
Thermal Resistance, Junction to Ambient	R _{θJA}	357	°C /W

**MMBD1201;MMBD1203
MMBD1204;MMBD1205**

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown voltage	Bv	I _R = 100 µA	100		V
Reverse current	I _R	I _F = 20 V		25	nA
		I _F = 50 V		50	nA
		I _F = 50 V, TA = 150 °C		5	µ A
Forward voltage	V _F	I _F = 1.0 mA	550	600	mV
		I _F = 10 mA	660	740	mV
		I _F = 100 mA	820	920	mV
		I _F = 200 mA	0.87	1.0	V
		I _F = 300 mA		1.1	V
Diode capacitance	C _D	V _R = 0, f = 1.0 MHz		2.0	pF
Reverse recovery time	T _{RR}	I _F = I _R = 10 mA, I _{RR} = 1.0 mA, R _L = 100 Ω		4.0	ns

■ Marking

Type	MMBD1201	MMBD1203	MMBD1204	MMBD1205
Marking	24	26	27	28